	Туре	L#	Hits	Search Text	DBs	Time Stamp	m e e ii nt ii s c	D Er of ro
1	BRS	L1	2	"20030096279"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:24		0
2	BRS	L2	2	"20030036279"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:05		0
3	BRS	L3	0	etch\$3 same (dorp with generator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:06		0
4	BRS	L4	43	etch\$3 same (drop with generator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:06		0
5	BRS	L5	197	etch\$3 and (drop with generator) and (print head)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:06		0
6	BRS	L6	26	(etch\$3 same (drop with generator)) and (print head)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:07		0
7	BRS	L7	27	(etch\$3 same (drop with generator)) and (printhead)	USPAT; US-PGPUB EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:20		0
8	BRS	L8	36	"5635966"	USPAT; US-PGPUB EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:00		0

	Туре	L#	Hits	Search Text	DBs	Time Stamp	C o m e nt	ef in	ro
9	BRS	L9	2456	Thermal and inkjet and printhead and (drop generator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:00			0
10	BRS	L10	846	9 and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:00			0
11	BRS	L11	406	10 and passivat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:01			0
12	BRS	L12	36	"5635966"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 12:27			0
13	BRS	L13	182928	(bi layer) same mask\$3	USPAT; US-PGPUB EPO; JPO; DERWENT; IBM_TDB				0
14	BRS	L14	145422	(bi layer) with mask\$3	USPAT; US-PGPUB EPO; JPO; DERWENT; IBM_TDB	2004/03/09 12:28			0
15	BRS	L15	14961	passiva\$4 and 14	USPAT; US-PGPUB EPO; JPO; DERWENT; IBM_TDB	2004/03/09 12:28			0
16	BRS	L16	89767	14 and (metal or conductive)	USPAT; US-PGPUB EPO; JPO; DERWENT; IBM_TDB	2004/03/09 12:34			0

	Туре	L#	Hits	Search Text	DBs	Time Stamp	C o m m	ın r	ro
17	BRS	L17	70969	16 and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 12:30		(Э
18	BRS	L18	42491	17 and @pd<=20010816	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 12:35		(0
19	BRS	L19	16689	18 and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 12:36		(0
20	BRS	L20	10509	(mask or pattern\$3) same (passivat\$4 or (psg or "phosphosilicate glass")) same etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 12:33		(0
21	BRS	L21	4571	20 same (metal or conductive)	USPAT; US-PGPUB EPO; JPO; DERWENT; IBM_TDB	2004/03/09 12:34		(0
22	BRS	L22	2654	21 and @pd<=20010816	USPAT; US-PGPUB EPO; JPO; DERWENT; IBM_TDB	2004/03/09 13:37		(0
23	BRS	L23	2538	(bi layer) and 22	USPAT; US-PGPUB EPO; JPO; DERWENT; IBM_TDB	2004/03/09 12:39			0
24	BRS	L24	1114	23 and 438/\$.ccls.	USPAT; US-PGPUB EPO; JPO; DERWENT; IBM_TDB	2004/03/09 13:38			0

	Туре	L#	Hits	Search Text	DBs	Time Stamp	C o m m	D ef in	ro
25	BRS	L25	129	24 and (drop generator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 12:37			0
26	BRS	L26	11	("bi layer") and 22	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 12:46			0
27	BRS	L27	8708	mask\$3 same (passivat\$3 or ((SiN or "Si.sub.3 N.sub.4" or "silicon nitride") and ("silicon carbide" or SiC)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 13:09			0
28	BRS	L28	5622	mask\$3 same (passivat\$3 or ((SiN or "Si.sub.3 N.sub.4" or "silicon nitride") and ("silicon carbide" or SiC))) same etch\$3	USPAT; US-PGPUB EPO; JPO; DERWENT; IBM_TDB	2004/03/09 13:12			0
29	BRS	L29	3246	28 and (deposit\$3 with (metal\$3 or conductive))	USPAT; US-PGPUB EPO; JPO; DERWENT; IBM_TDB	2004/03/09 13:12			0
30	BRS	L30	3246	28 and (deposit\$3 with (metal\$3 or conductive))	USPAT; US-PGPUB EPO; JPO; DERWENT; IBM_TDB	² 2004/03/09 13:37			0
31	BRS	L31	1662	29 and @pd<=20010816	USPAT; US-PGPUB EPO; JPO; DERWENT IBM_TDB	, 2004/03/09 13:37			0
32	BRS	L32	822	31 and 438/\$.ccls.	USPAT; US-PGPUB EPO; JPO; DERWENT IBM_TDB	; 2004/03/09 13:38			0

	Туре	L#	Hits	Search Text	DBs	Time Stamp	C o m m	ef in	Er ro	þ
33	BRS	L33	117		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 13:38			0	